

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1.-16. (Canceled)

17. (Currently Amended) A method of manufacturing a semiconductor device, including the steps of:

attaching a semiconductor die to a substrate;

positioning a housing on the substrate, in a position surrounding the die;

positioning a mold over the housing such that an upper surface of the housing abuts against an inner surface of the mold; and

injecting into the mold a molding material to secure the housing to the substrate.

18. (Original) The method of claim 17 further including the step of wire bonding the semiconductor die to selected pads on the substrate.

19. (Original) The method of claim 17 wherein the step of attaching a semiconductor die to a substrate includes the step of applying an adhesive substance to the substrate prior to applying the semiconductor die.

20. (Original) The method of claim 17 wherein the step of injecting a molding material includes the step of bringing the molding material to a temperature in the range of 160°C-185°C and a pressure of 75bar $\pm 10\%$ before it is injected into the mold.

21. (Original) The method of claim 17 wherein the step of positioning the housing includes positioning the housing in a channel that surrounds the semiconductor die.

22. (Original) The method of claim 17 wherein the step of positioning the housing includes penetrating part of the substrate with a portion of the housing.

23. (Original) The method of claim 17 wherein an inner surface of the mold is arranged to be deformable such that a tight fit against the upper surface of the housing is achieved.

Claims 24.-34. (Canceled)

35. (New) A method of manufacturing a semiconductor device having a substrate and a die attached to the substrate, the method comprising:

placing a housing on the substrate to cover the die;

positioning a mold over the housing so that the mold bears against the housing;

and

injecting a molding material into the mold to secure the housing to the substrate.

36. (New) The method of claim 35, wherein positioning the mold over the housing comprises urging the mold against the housing to deform at least a portion of the mold.

37. (New) The method of claim 35 further including the step of wire bonding the semiconductor die to selected pads on the substrate.

38. (New) The method of claim 35 wherein the step of injecting a molding material includes the step of bringing the molding material to a temperature in the range of 160°C-185°C and a pressure of 75bar \pm 10% before it is injected into the mold.

39. (New) The method of claim 35 wherein the step of positioning the housing includes positioning the housing in a channel that surrounds the semiconductor die.

40. (New) The method of claim 35 wherein the step of positioning the housing includes penetrating part of the substrate with a portion of the housing.

41. (New) The method of claim 35 wherein an inner surface of the mold is arranged to be deformable such that a tight fit against the upper surface of the housing is achieved.

42. (New) A method of manufacturing a semiconductor device, comprising:
placing a housing on a substrate in a position to surround a semiconductor die on the substrate;

positioning a mold over the housing such that an upper surface of the housing abuts against an inner surface of the mold so that at least a portion of the mold is deformed to achieve a tight fit against the upper surface of the housing; and

securing the housing to the substrate by injecting a molding material into the mold.

43. (New) The method of claim 42, further comprising wire bonding the semiconductor die to selected pads on the substrate prior to positioning the housing on the substrate.

44. (New) The method of claim 42 wherein positioning the housing includes penetrating part of the substrate with a portion of the housing.

45. (New) The method of claim 42 wherein securing the housing to the substrate by injecting molding material into the mold comprises bringing the molding material to a temperature in the range of 160°C-185°C and a pressure of 75bar \pm 10% before it is injected into the mold.